

isc Silicon NPN Power Transistors

2SD458

DESCRIPTION

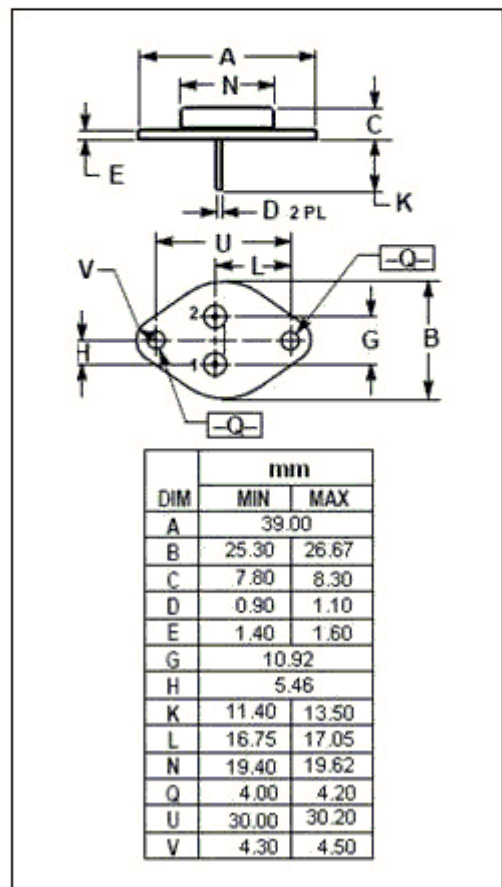
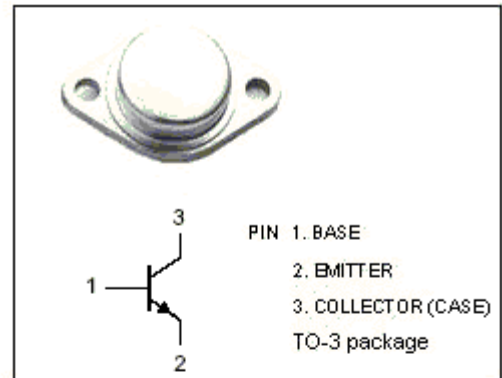
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 400V(\text{Min})$
- High Power Dissipation-
: $P_C = 80W(\text{Max}) @ T_C = 25^\circ\text{C}$

APPLICATIONS

- Designed for high power amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	600	V
V_{CER}	Collector-Emitter Voltage $R_{BE} = 50 \Omega$	600	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current-Continuous	2	A
I_{BM}	Base Current-Peak	3	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	80	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$



isc Silicon NPN Power Transistors**2SD458****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; I _B = 0	400			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 1A			1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 1A			3.0	V
I _{CER}	Collector Cutoff Current	V _{CE} = 600V; R _{BE} = 50 Ω			1.0	mA
h _{FE}	DC Current Gain	I _C = 5A; V _{CE} = 5V	6.5		50	

◆ **h_{FE} Classifications**

Q	R
15-50	6.5-30